

## ABSTRACT

The present invention is provided to manufacture a method of manufacturing a semiconductor device, comprising the steps of: forming a first well region by performing an ion implantation process for implanting first  
5 ions into a semiconductor substrate, and then forming a second well region in the first well region by performing an ion implantation process for implanting second ions having larger mass than the first ions; and forming a well region by performing an annealing process on the result structure. Therefore, it is possible to prevent TED phenomenon generated due to the high-energy heat  
10 treatment process to be performed later and to provide the increased activation ratio of ions compared to the conventional source/drain region in which only the ions having large mass are implanted by performing an annealing process after the first well region and the second well region are formed.